

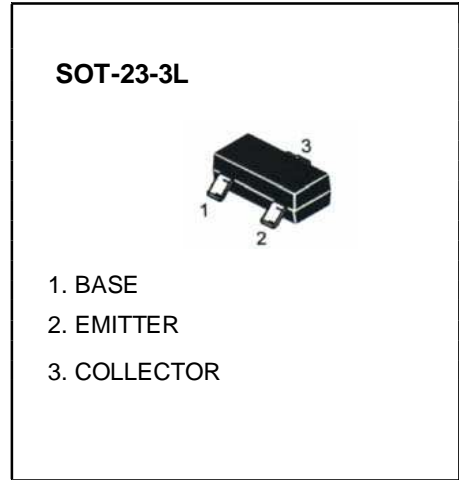


SOT-23 Plastic-Encapsulate Transistors

2SC3356 TRANSISTOR (NPN)

FEATURES

- Low noise amplifier at VHF, UHF and CATV band.
- Low Noise and High Gain
- High Power Gain



MAXIMUM RATINGS (T_A=25; unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector- Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	3	V
I _c	Collector Current -Continuous	0.1	A
P _c	Collector Power Dissipation	0.25	W
T _J	Junction Temperature	150	
T _{stg}	Storage Temperature	-55-150	

ELECTRICAL CHARACTERISTICS (T_{amb}=25; unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =10uA, I _E =0	20			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = 1mA, I _B =0	12			V
Collector cut-off current	I _{CBO}	V _{CB} =10V, I _E =0			1	uA
Emitter cut-off current	I _{EBO}	V _{EB} =1V, I _c =0			1	uA
DC current gain	h _{FE} [*]	V _{CE} =10V, I _c = 20mA	50		250	
Transition frequency	f _T	V _{CE} =10V, I _c = 20mA		î		GHz
Noise figure	NF	V _{CE} =10V, I _c = 7mA, f = 1GHz			2	dB

CLASSIFICATION OF hFE

Marking	R23	R24	R25
Rank	Q	R	S
Range	50-100	80-160	125-250

Typical Characteristics

2SC3356

